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AMENDMENTS TO THE SPECIFICATION:

Please amend the first full paragraph on page 3 as follows:

~~According to~~ In their Extended Abstracts (The 46th Spring Meeting, 1999; page 416); ~~The, the~~ Japan Society of Applied Physics and Related Societies, ~~page 416~~, disclosed is a method in which a base layer made of gallium nitride (GaN) or the like is formed over a sapphire (Al_2O_3) basal body, and a recessed region is formed in the surface of the base layer, and a gallium nitride (GaN) crystal is grown over the surface of the base layer. Since the method causes a change in the direction of the development of a dislocation at the recessed region of the base layer, the number of dislocations piercing the crystal reduces to some extent. In the method, however, dislocations developing off the recessed region of the base layer pierce the crystal. Thus, the method has a problem that the number of dislocations piercing the crystal cannot be reduced sufficiently.

Please amend the paragraph beginning on line 19 of page 3 as follows:

On the other hand, ~~according to~~ MRS Internet J. Nitride Semicond. Res. 4S1, G3. 38 (1999) and MRS Internet J. Nitride Semicond. Res. 4S1, G4. 9 (1999)[[.]] proposed are methods of preventing dislocations piercing the crystal using lateral growth. In the former method, a gallium nitride (GaN) crystal as a seed crystal is etched to form a groove, and the crystal growth is re-started in the lateral direction from the walls of the groove. In the latter method, a mask pattern for etching is formed on the surface of a gallium nitride (GaN) crystal as a seed crystal, and the crystal growth is re-started in the lateral direction from the walls of the groove, while the mask pattern prevents the crystal growth over the surface of the seed crystal. However, with the former method, there is a possibility that dislocations will develop from the surface of the seed crystal. With the latter method, there is a possibility

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that new dislocations will develop above the mask pattern. Thus, both methods have a problem that dislocations piercing the crystal cannot be prevented sufficiently.

Please amend the first full paragraph on page 6 as follows:

In the method of manufacturing a crystal of a III-V compound of the nitride system, the crystal substrate of a III-V compound of the nitride system, the crystal film of a III-V compound of the nitride system and the method of manufacturing a device according to the invention, it is ensured that the development of dislocations is prevented in a region where a plurality of patterns do not overlie one another in the direction of the thickness of the crystal. Moreover, there ~~are~~ is a region where the patterns overlie one another and a region where the patterns do not overlie one another, and both regions coexist. This causes a region where the plurality of patterns do not overlie one another (that is, a region where it is ensured that the development of dislocations is prevented) to be provided without accurate alignment of the patterns.